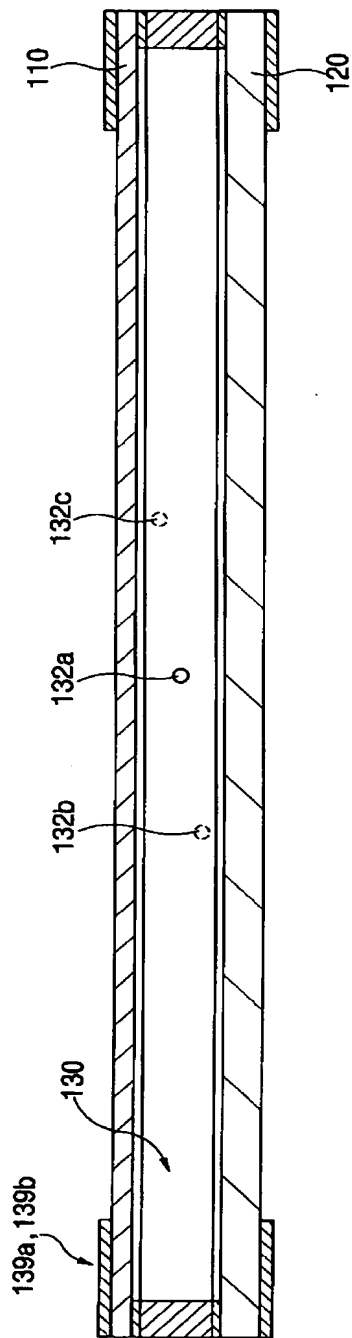
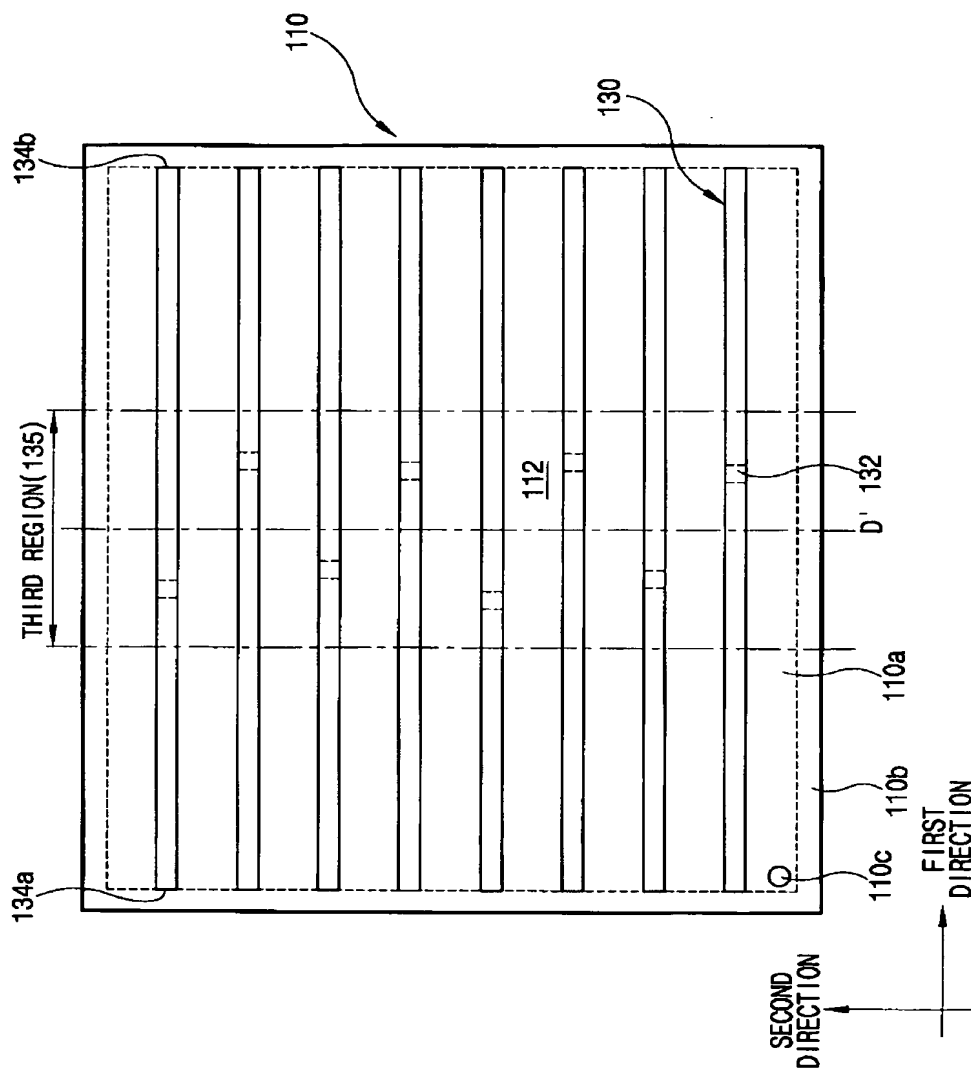




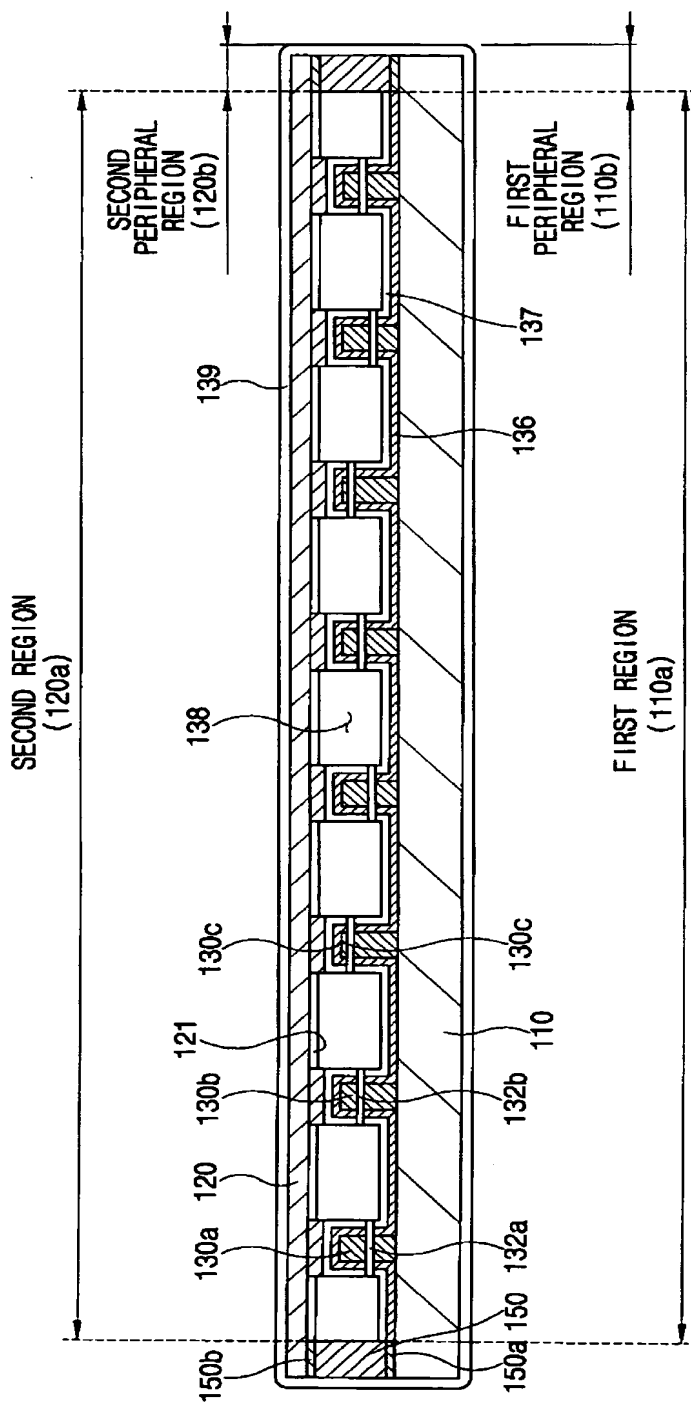
[Fig. 2]



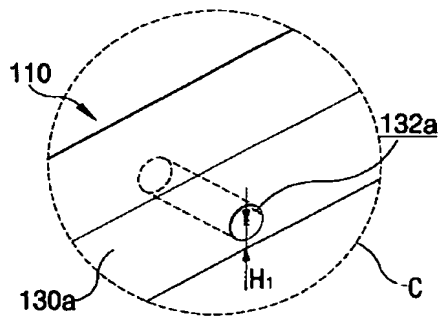
[Fig. 3]



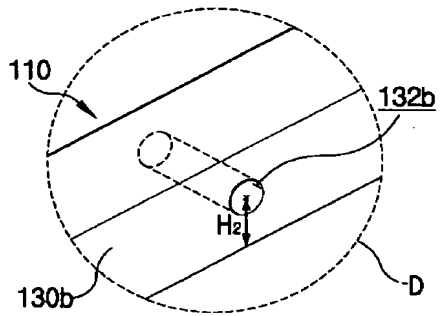
[Fig. 4]



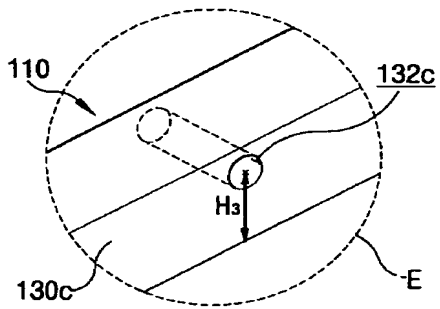
[Fig. 5]



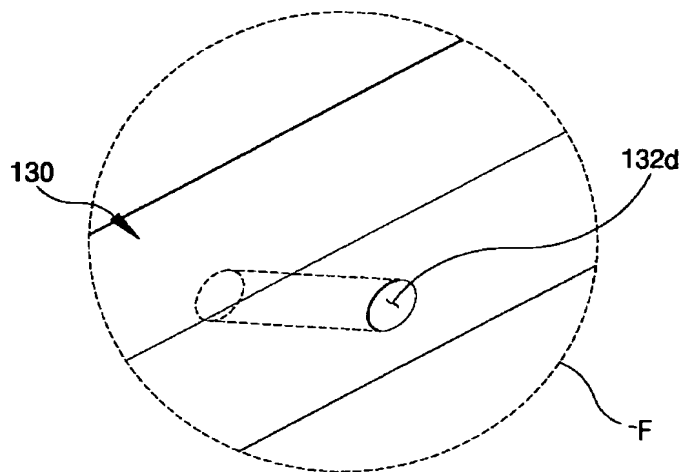
[Fig. 6]



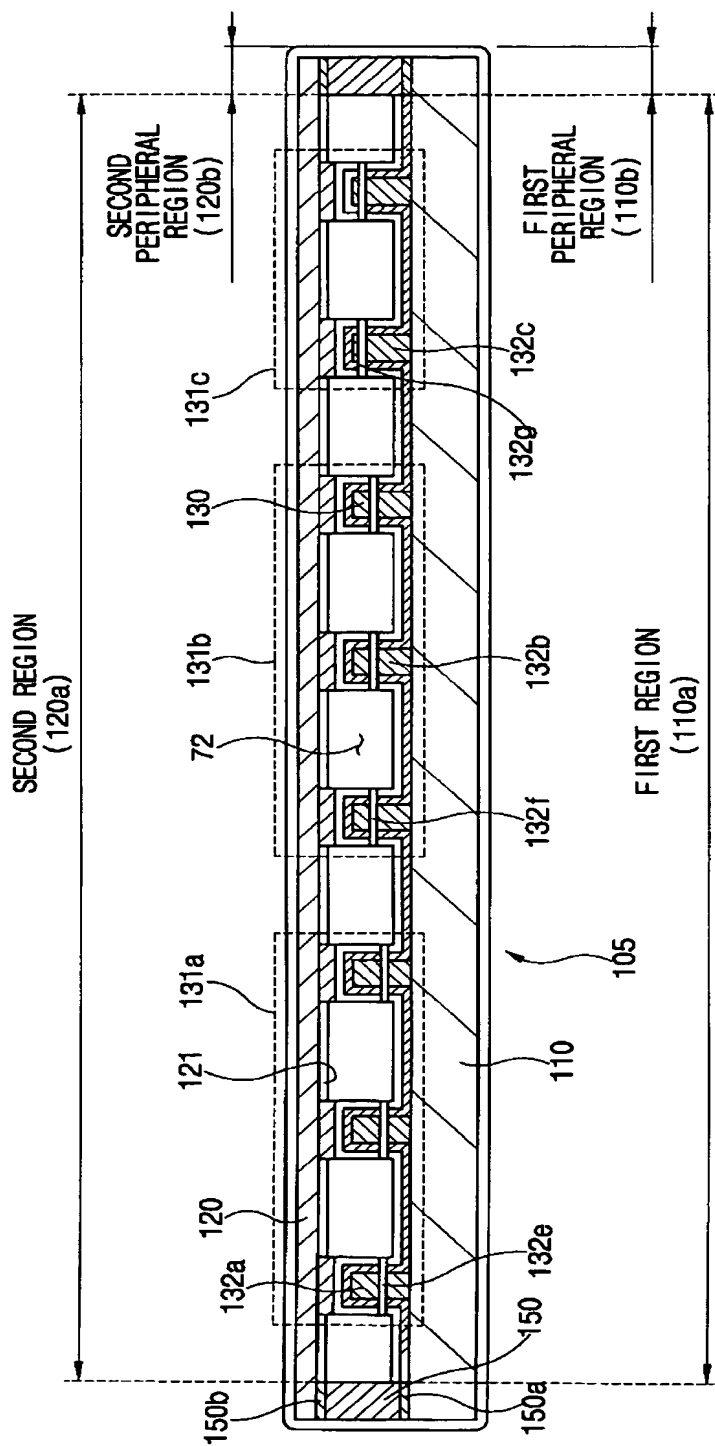
[Fig. 7]



[Fig. 8]



[Fig. 9]



A cross-sectional view of a semiconductor device. The device consists of a central channel region (105) flanked by two peripheral regions: a first peripheral region (110b) on the left and a second peripheral region (120b) on the right. The channel region (105) contains a series of rectangular blocks (130a, 130b, 130c) separated by thin layers (133). The peripheral regions (110b, 120b) contain a series of rectangular blocks (150a, 150b) separated by thin layers (153). The device is bounded by a top layer (100) and a bottom layer (101). The first region (110a) is the area between the first peripheral region (110b) and the channel region (105). The second region (120a) is the area between the second peripheral region (120b) and the channel region (105). The first region (110a) contains a series of rectangular blocks (112) separated by thin layers (113). The second region (120a) contains a series of rectangular blocks (121) separated by thin layers (123). The device is also labeled with 150a, 150b, 153, 130a, 130b, 130c, 133, 112, 121, 113, 123, 100, and 101.



[Fig. 11]

